

DARLINGTON AMPLIFIERS

Type NPN	Maximum Ratings				Electrical Characteristics @ 25°C						Case
	P _D Ambient mW	V _{CB} Volts	V _{CE} Volts	V _{EB} Volts	H _{FE} @ I _C		V _{CE} (Sat) @ I _C /I _B		f _t MHz Min	C _{ob} pF Max	
					Min/Max	mA	Volts	mA/mA			
2N997	500	75	40	7	7000/70,000	100	1.6	100/10	60*	30	TO-18
2N998	500	100	60	15	1600/8000	10	1.8	100/10	60*	30	TO-72
2N999	500	60	60	15	7000/70,000	100	1.6	100/10	60*	20	TO-72
2N2723	500	80	60	12	2000/10,000	10	1.0	10/1	100	10	TO-72
2N2724	500	80	60	12	7000/50,000	10	1.0	10/1	100	10	TO-72
2N2725	500	45	45	10	2000/10,000	0.1	1.0	10/1	100	10	TO-72

UHF HIGH POWER AMPLIFIERS

This line is in final development stage and will be introduced early 1969.

Type NPN	P _D Ambient Watts	V _{CB} Volts	V _{CE} Volts	V _{EB} Volts	H _{FE} @ I _C		V _{CE} (Sat) @ I _C /I _B		f _t MHz Min	C _{ob} pF Max	P _O @ f		Case
					Min/Max	mA	Volts	mA/mA			Watts Min	MHz	
2N3375	11.6	65	40	4	10/100	250	1.0	250/50	350	12	3	400	TO-60
2N3553	7	65	40	4	10/100	250	1.0	250/50	350	12	2.5	175	TO-39
2N3632	23	65	40	4	10/150	250	1.0	1000/200	250	25	13.5	175	TO-60
2N3733	23	65	40	4	10/150	250	1.0	1000/200	250	25	10	400	TO-60
2N4440	11.6	65	40	4	10/200	125	1.0	250/50	400	12	5	400	TO-60
2N5016	30	65	30	4	10/200	500	—	—	600	25	15	400	TO-60
2N5108	3.5	55	55 ¹	3	60 ²	100	—	—	1200	3	1	1000	TO-39

¹BV_{CEB} ≤ 10Ω

²Typical Value

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